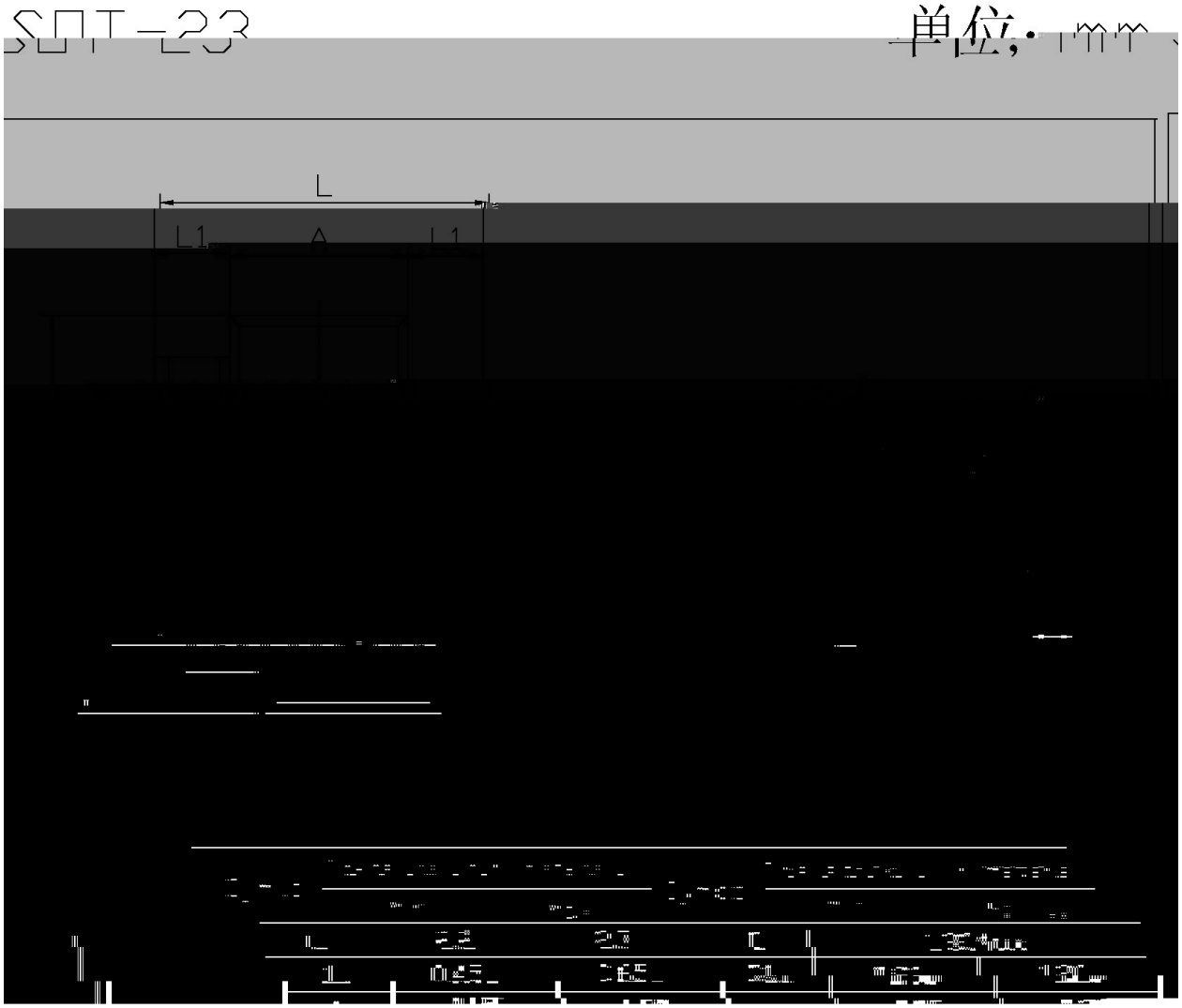
/ Absolute Maximum Ratings(Ta=25)

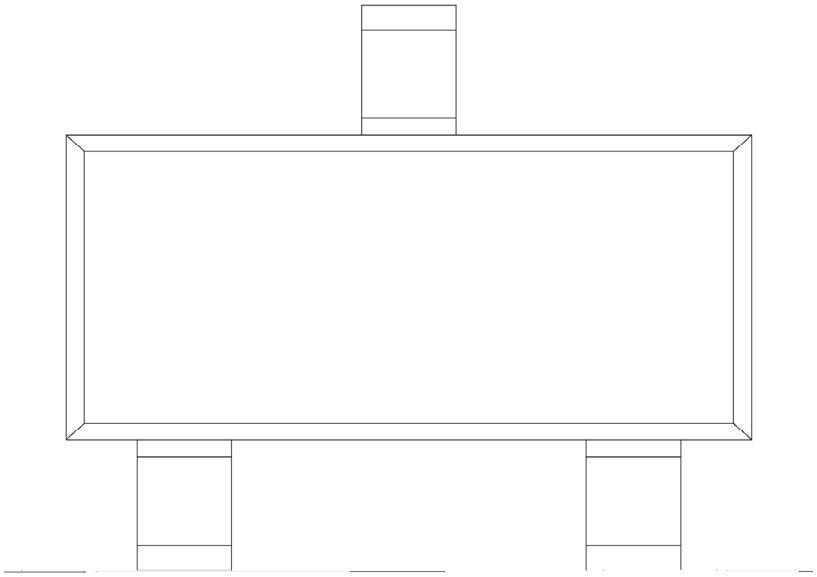
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	50	V
Collector to Emitter Voltage	V_{CEO}	30	V
Emitter to Base Voltage	V_{EBO}	5.0	V
Collector Current	I_C	30	mA
Base Current	I_B	10	mA
Collector Power Dissipation	P_C	310	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

/ Electrical Characteristics(Ta=25)

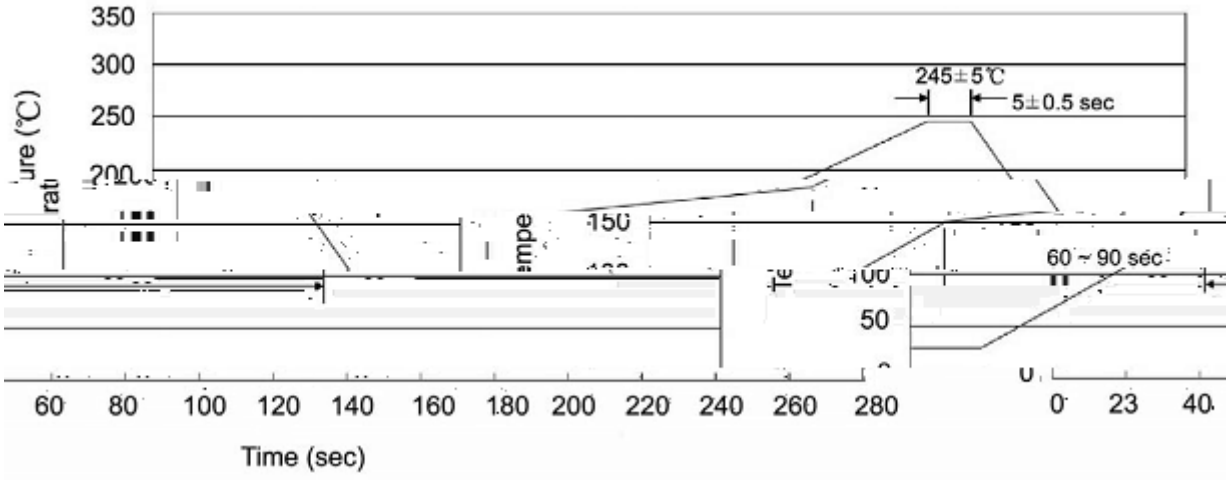
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	I_C=0.1mA I_E=0	50			V
Collector to Emitter Breakdown Voltage	V_{CEO}	I_C=1.0mA I_B=0	30			V
Emitter to Base Breakdown Voltage	V_{EBO}	I_E=0.1mA I_C=0	5.0			V
Collector Cut-Off Current	I_{CBO}	V_{CB}=50V I_E=0			0.1	μA
Emitter Cut-off Current	I_{EBO}	V_{EB}=5.0V I_C=0			0.1	μA
DC Current Gain	h_{FE}	V_{CE}=5.0V I_C=1.0mA	28		198	
Collector-Emitter Saturation voltage	$V_{CE(sat)}$	I_C=10mA I_B=1.0mA		0.08	0.3	V
Base-Emitter Voltage	V_{BE}	V_{CE}=5.0V I_C=1.0mA		0.7	0.75	V
Current Gain Bandwidth Product	f_T	V_{CE}=5.0V I_C=1.0mA	150	370		MHz
Output Capacitance	C_{ob}	V_{CB}=10V I_E=0 f=1.0MHz		1.5		pF
Noise Figure	NF	V_{CE}=5.0V I_C=1.0mA R_g=500Ω f=1.0MHz		2.0	4.0	dB

/ Package Dimensions





( ) / Temperature Profile for IR Reflow Soldering(Pb-Free)



Note:

1	25	150	60	90sec;
2	245±5			5±0.5sec;
3		2	10	/sec.

1.Preheating:25~150 , Time:60~90sec.
2.Peak Temp.:245±5 , Duration:5±0.5sec.
3. Cooling Speed: 2~10 /sec.

/ Resistance to Soldering Heat Test Conditions

260±5	10±1 sec.	Temp.:260±5	Time:10±1 sec

/ Packaging SPEC.